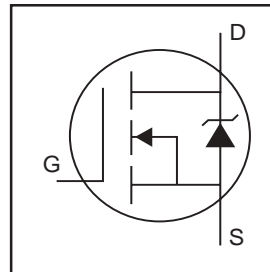


**Features**

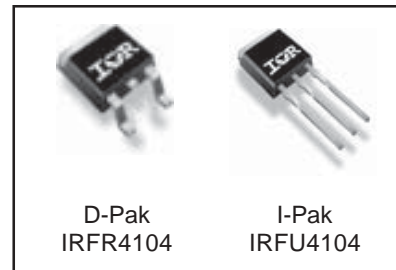
- Advanced Process Technology
- Ultra Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax



$V_{DS} = 40V$
$R_{DS(on)} = 5.5m\Omega$
$I_D = 42A$

**Description**

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.



**Absolute Maximum Ratings**

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Silicon Limited)	119	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	84	
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Package Limited)	42	
$I_{DM}$	Pulsed Drain Current ①	480	
$P_D @ T_C = 25^\circ C$	Power Dissipation	140	W
	Linear Derating Factor	0.95	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$ (Thermally limited)	Single Pulse Avalanche Energy ②	145	mJ
$E_{AS}$ (Tested )	Single Pulse Avalanche Energy Tested Value ③	310	
$I_{AR}$	Avalanche Current ④	See Fig.12a, 12b, 15, 16	A
$E_{AR}$	Repetitive Avalanche Energy ⑤		mJ
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	
	Mounting Torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.05	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount) ⑥	—	40	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

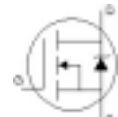
HEXFET® is a registered trademark of International Rectifier.

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	40	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.032	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	4.3	5.5	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 42A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	58	—	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 42A
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	20	μA	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	200	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-200		V <sub>GS</sub> = -20V
Q <sub>g</sub>	Total Gate Charge	—	59	89	nC	I <sub>D</sub> = 42A
Q <sub>gs</sub>	Gate-to-Source Charge	—	19	—		V <sub>DS</sub> = 32V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	24	—		V <sub>GS</sub> = 10V ③
t <sub>d(on)</sub>	Turn-On Delay Time	—	17	—	ns	V <sub>DD</sub> = 20V
t <sub>r</sub>	Rise Time	—	69	—		I <sub>D</sub> = 42A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	37	—		R <sub>G</sub> = 6.8 Ω
t <sub>f</sub>	Fall Time	—	36	—		V <sub>GS</sub> = 10V ③
L <sub>D</sub>	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L <sub>S</sub>	Internal Source Inductance	—	7.5	—		
C <sub>iss</sub>	Input Capacitance	—	2950	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	660	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	370	—		f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	2130	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 1.0V, f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	590	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 32V, f = 1.0MHz
C <sub>oss eff.</sub>	Effective Output Capacitance	—	850	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 32V ④

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	42	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	480		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 42A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	28	42	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 42A, V <sub>DD</sub> = 20V
Q <sub>rr</sub>	Reverse Recovery Charge	—	24	36	nC	di/dt = 100A/μs ③
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				



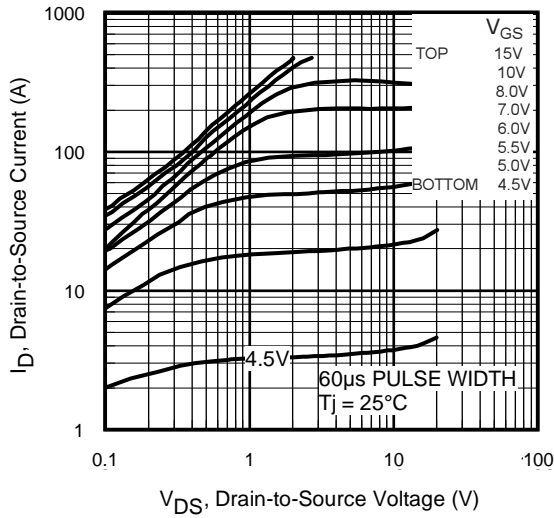


Fig 1. Typical Output Characteristics

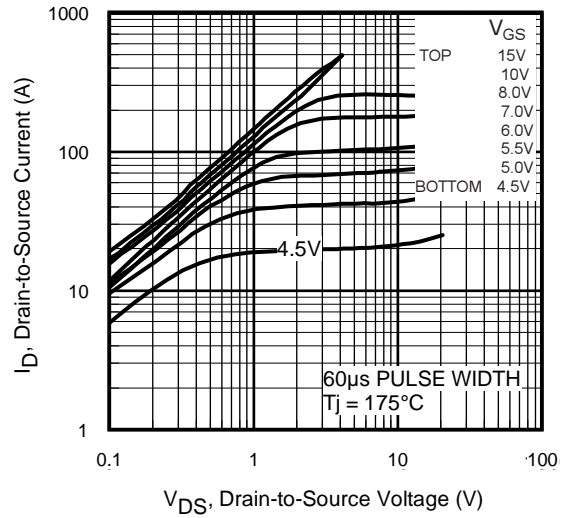


Fig 2. Typical Output Characteristics

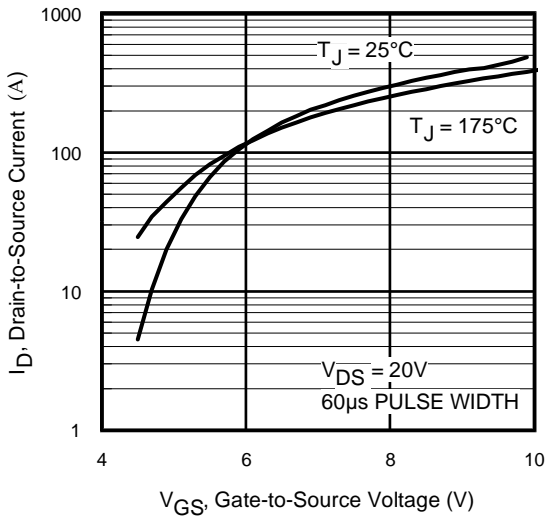


Fig 3. Typical Transfer Characteristics

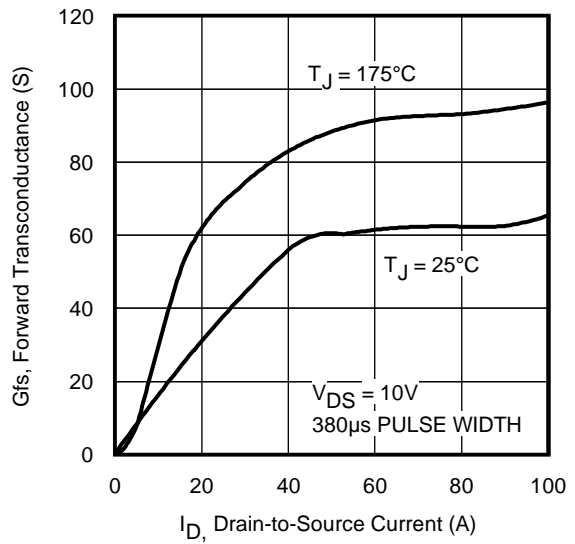
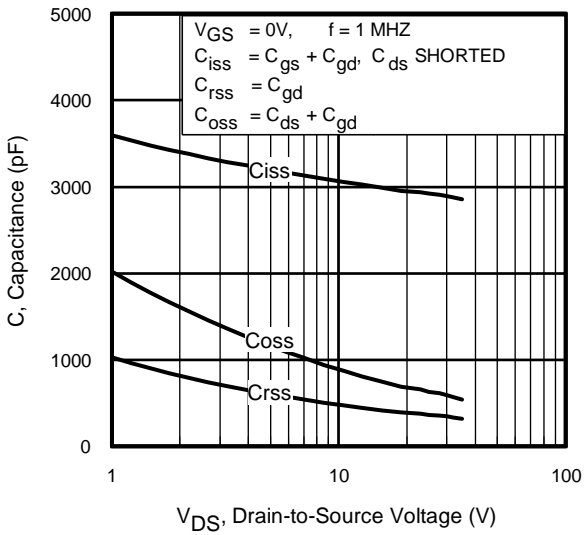
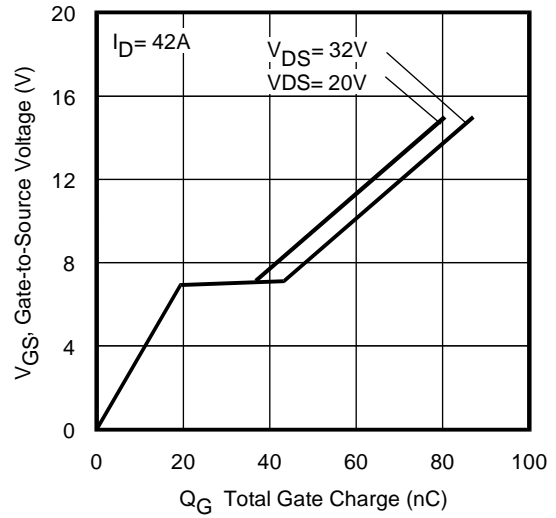


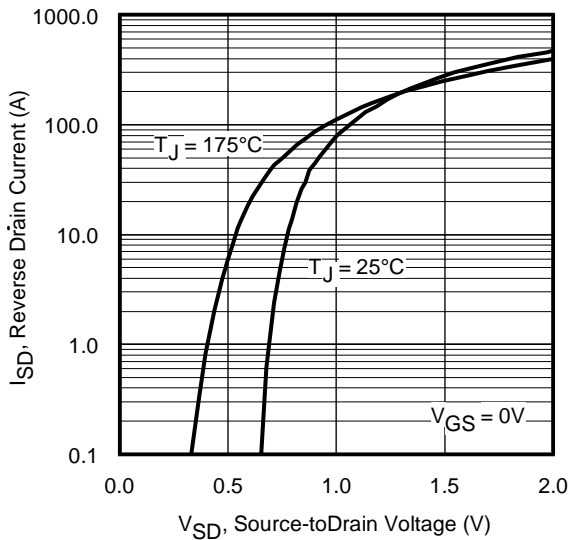
Fig 4. Typical Forward Transconductance Vs. Drain Current



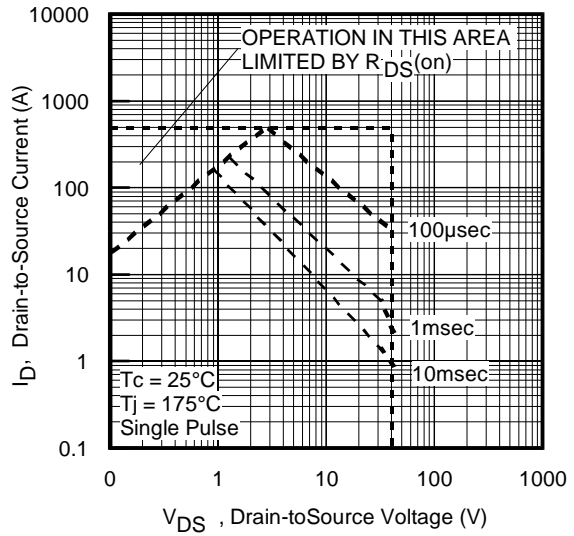
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

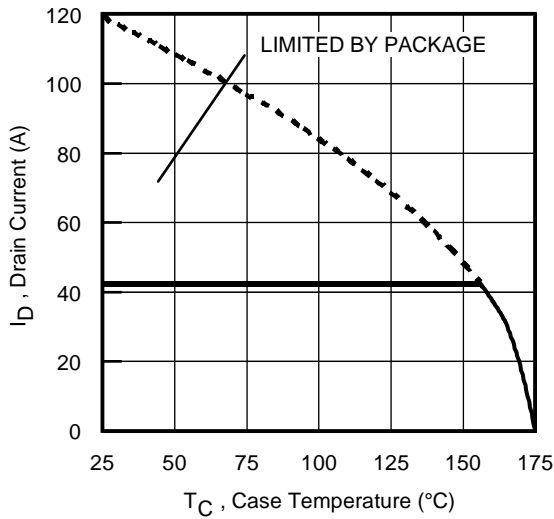


Fig 9. Maximum Drain Current Vs. Case Temperature

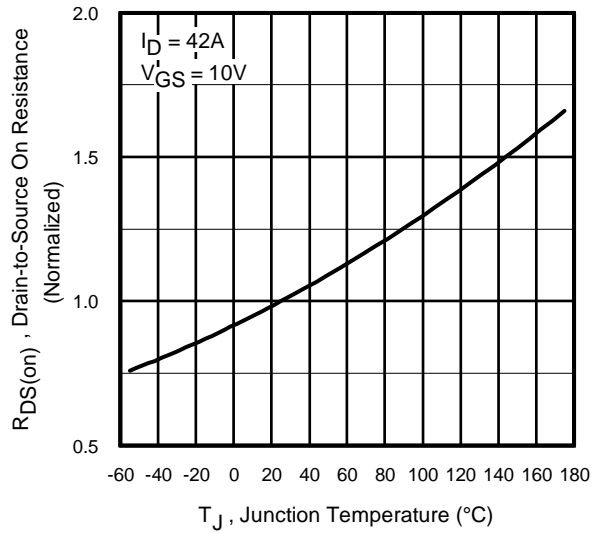


Fig 10. Normalized On-Resistance Vs. Temperature

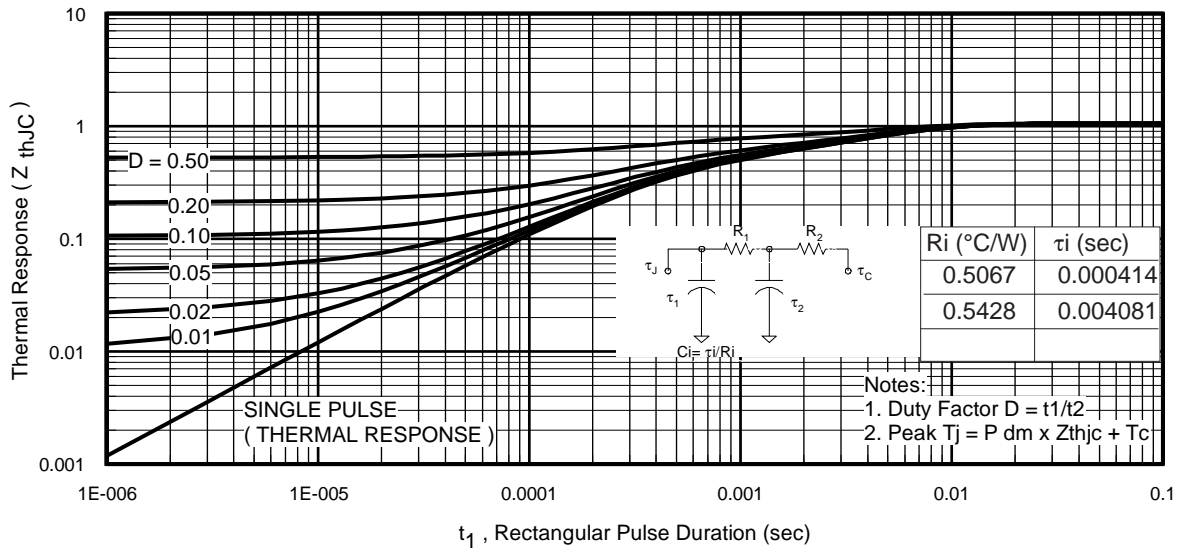
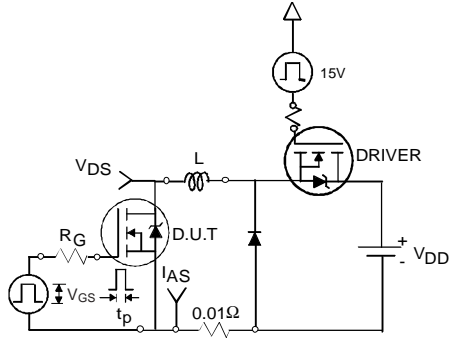
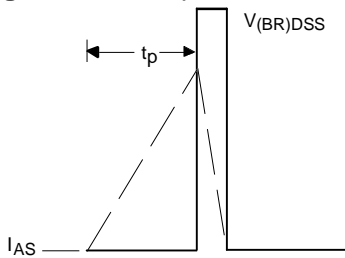


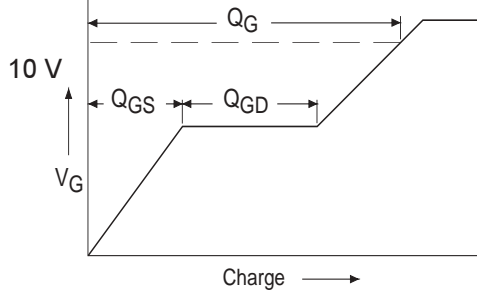
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case



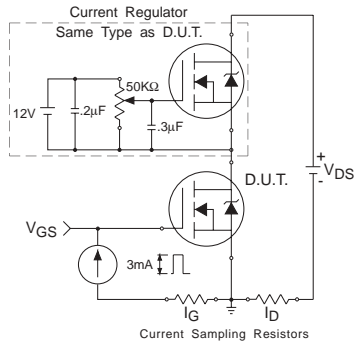
**Fig 12a.** Unclamped Inductive Test Circuit



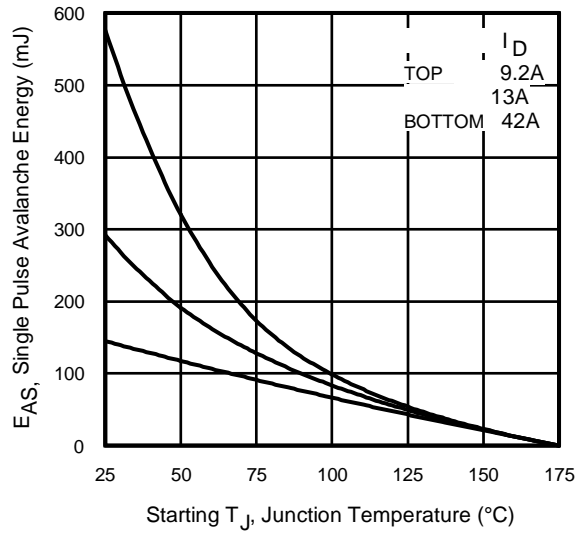
**Fig 12b.** Unclamped Inductive Waveforms



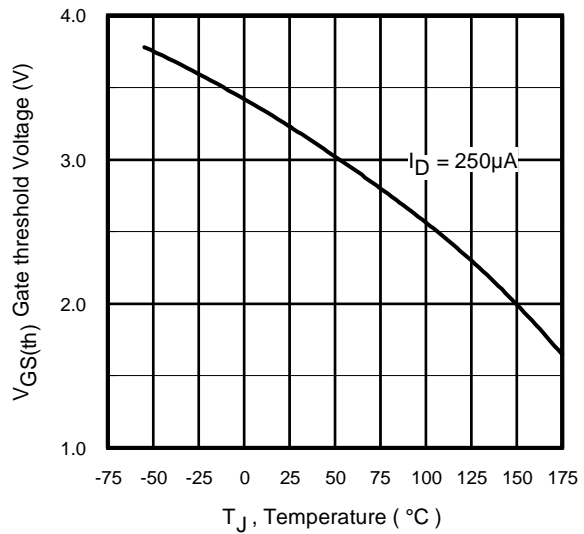
**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 14.** Threshold Voltage Vs. Temperature

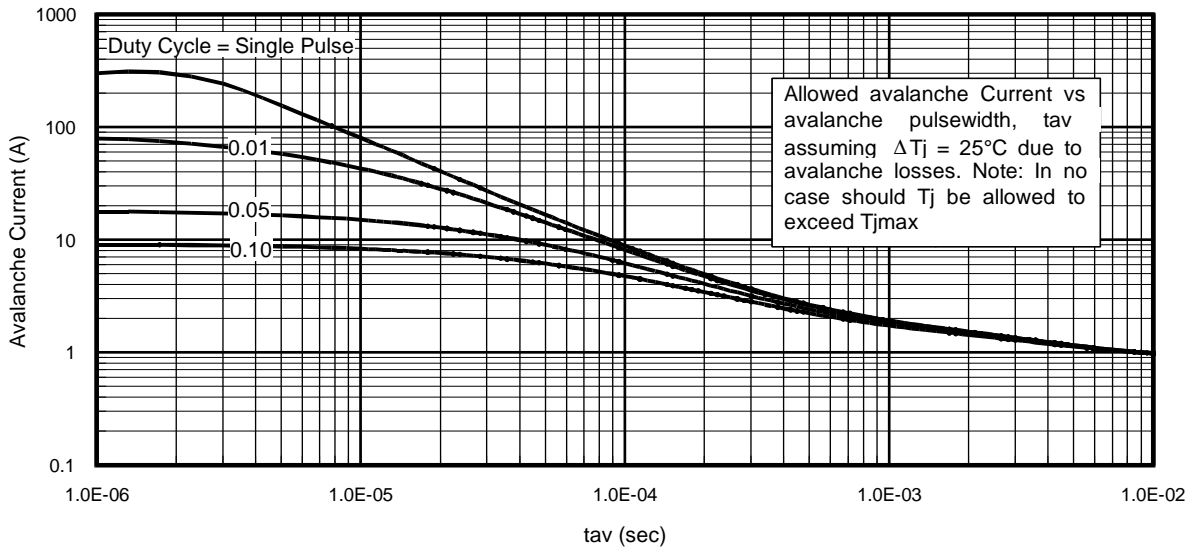


Fig 15. Typical Avalanche Current Vs.Pulsewidth

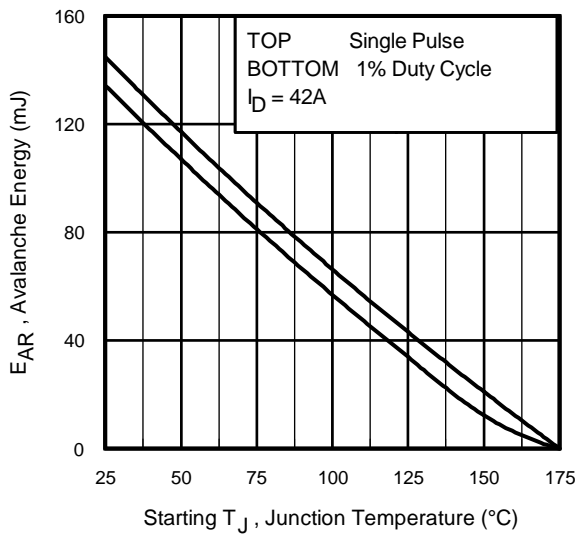


Fig 16. Maximum Avalanche Energy Vs. Temperature

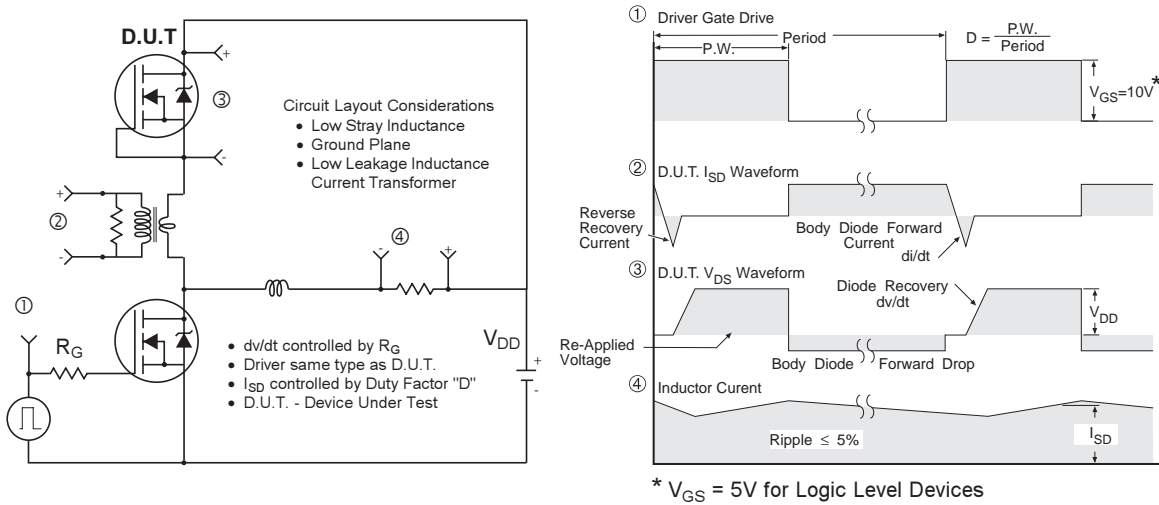
**Notes on Repetitive Avalanche Curves , Figures 15, 16:**  
(For further info, see AN-1005 at [www.irf.com](http://www.irf.com))

1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 15, 16).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see figure 11)

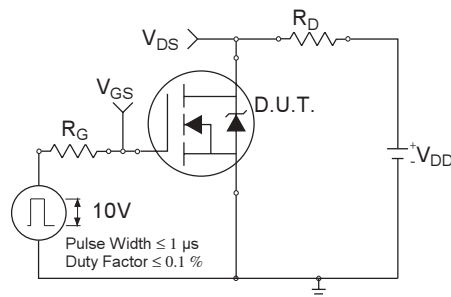
$$P_{D(ave)} = 1/2 ( 1.3 \cdot BV \cdot I_{av} ) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

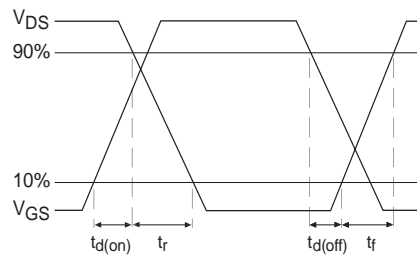
$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$



**Fig 17. Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs**



**Fig 18a. Switching Time Test Circuit**

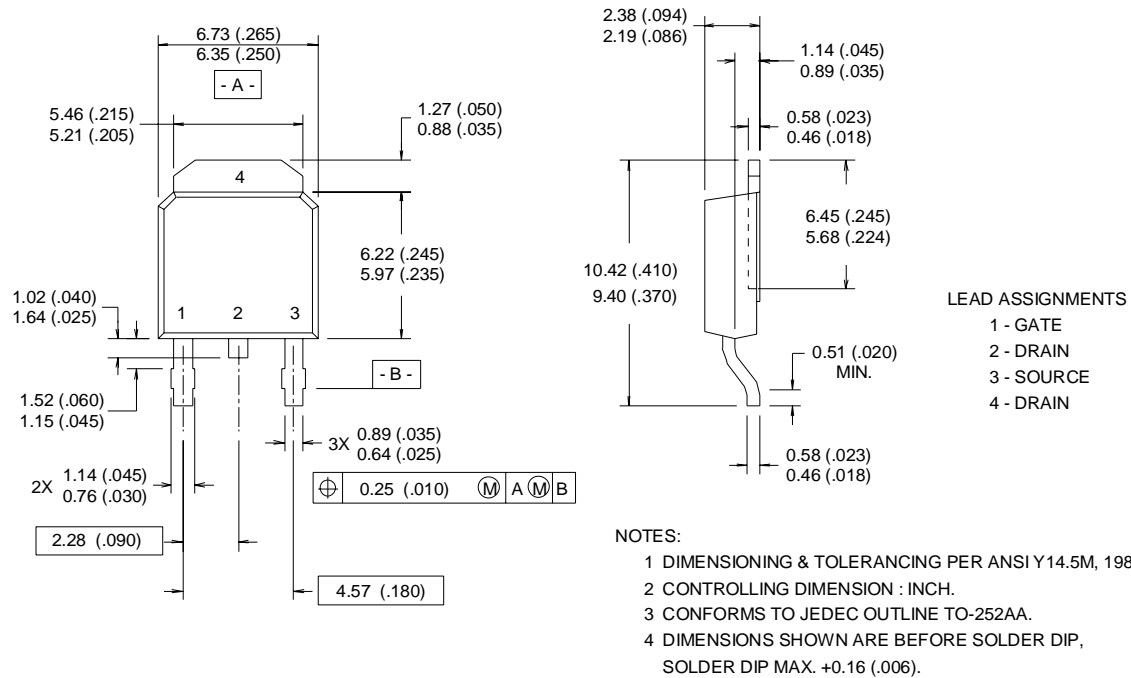


**Fig 18b. Switching Time Waveforms**



## D-Pak (TO-252AA) Package Outline

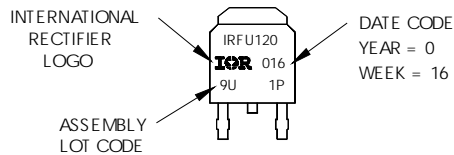
Dimensions are shown in millimeters (inches)



## D-Pak (TO-252AA) Part Marking Information

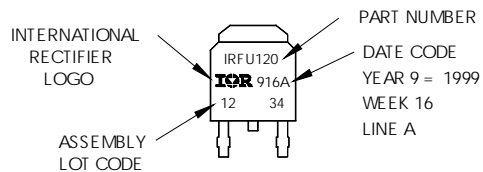
Notes: This part marking information applies to devices produced before 02/26/2001

EXAMPLE: THIS IS AN IRFR120  
 WITH ASSEMBLY  
 LOT CODE 9U1P



Notes: This part marking information applies to devices produced after 02/26/2001

EXAMPLE: THIS IS AN IRFR120  
 WITH ASSEMBLY  
 LOT CODE 1234  
 ASSEMBLED ON WW 16, 1999  
 IN THE ASSEMBLY LINE "A"

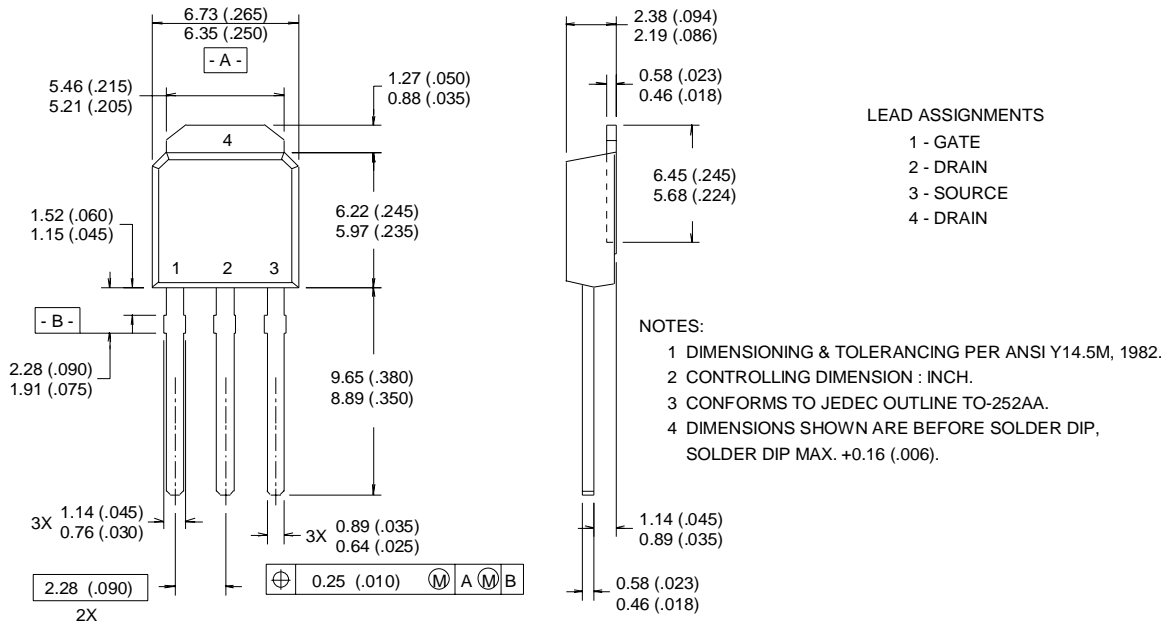


# IRFR/U4104

## I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)

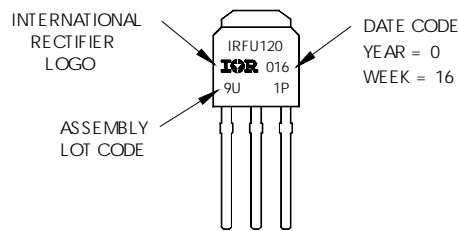
International  
**IR** Rectifier



## I-Pak (TO-251AA) Part Marking Information

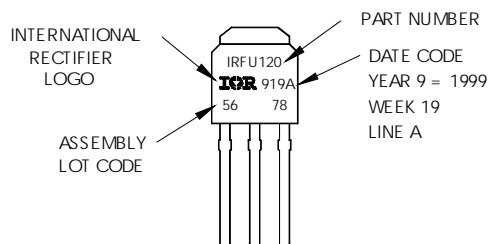
Notes: This part marking information applies to devices produced before 02/26/2001

EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 9U1P



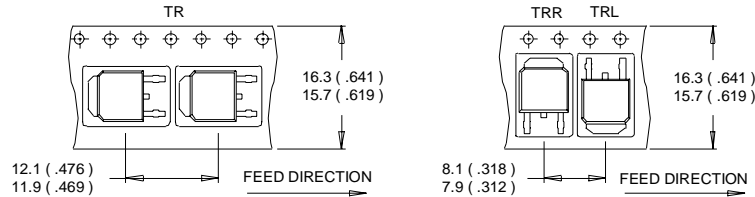
Notes: This part marking information applies to devices produced after 02/26/2001

EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 5678  
ASSEMBLED ON WW 19, 1999  
IN THE ASSEMBLY LINE "A"

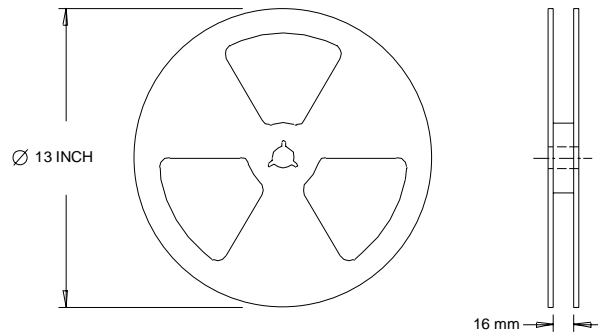


## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. OUTLINE CONFORMS TO EIA-481.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② Limited by  $T_{Jmax}$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.16\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 42\text{A}$ ,  $V_{GS} = 10\text{V}$ . Part not recommended for use above this value.
- ③ Pulse width  $\leq 1.0\text{ms}$ ; duty cycle  $\leq 2\%$ .
- ④  $C_{OSS}$  eff. is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑤ Limited by  $T_{Jmax}$ , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
- ⑥ This value determined from sample failure population. 100% tested to this value in production.
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994

Data and specifications subject to change without notice.  
 This product has been designed and qualified for the Automotive [Q101] market.  
 Qualification Standards can be found on IR's Web site.